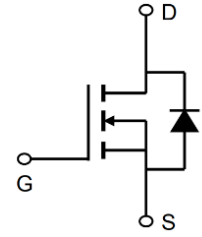


30V N-Channel Enhancement Mode MOSFET

Description

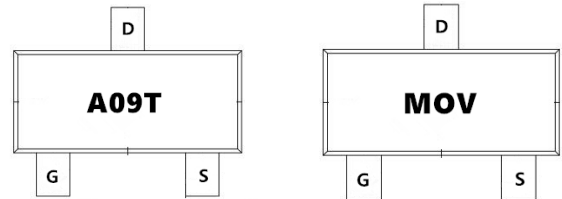
The AP3400AI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 30V$ $I_D = 5.8A$

$R_{DS(ON)} < 28m\Omega$ @ $V_{GS}=10V$



Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP3400AI	SOT-23	A09T	3000
AP3400AI	SOT-23	MOV	3000

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current	5.8	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current	4.9	A
IDM	Pulsed Drain Current ²	20	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10\text{s}$)	85	$^\circ\text{C}/\text{W}$

30V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	33	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.029	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5.8A	---	20	28	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =5A	---	24	32	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =2.5V, I _D =4A	---	31	55	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.85	1.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-2.82	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	---	25	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =5.8A	---	11.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.6	---	
Q _{gd}	Gate-Drain Charge		---	2.9	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3Ω I _D =5A	---	5	---	ns
T _r	Rise Time		---	47.	---	
T _{d(off)}	Turn-Off Delay Time		---	26	---	
T _f	Fall Time		---	8	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	860	---	pF
C _{oss}	Output Capacitance		---	84	---	
C _{rss}	Reverse Transfer Capacitance		---	70	---	
I _s	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	5.8	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1、.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

30V N-Channel Enhancement Mode MOSFET

Typical Characteristics

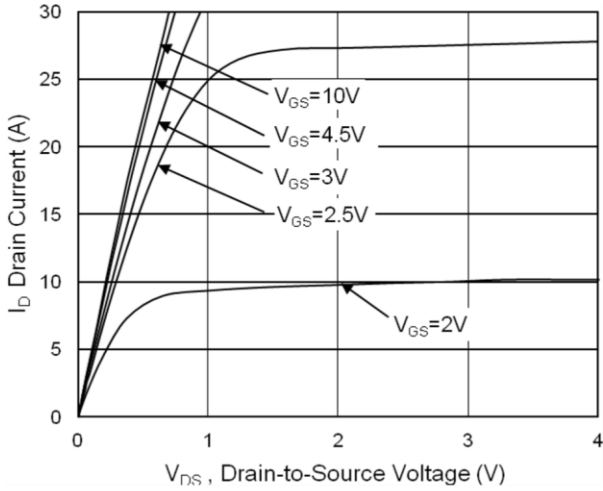


Fig.1 Typical Output Characteristics

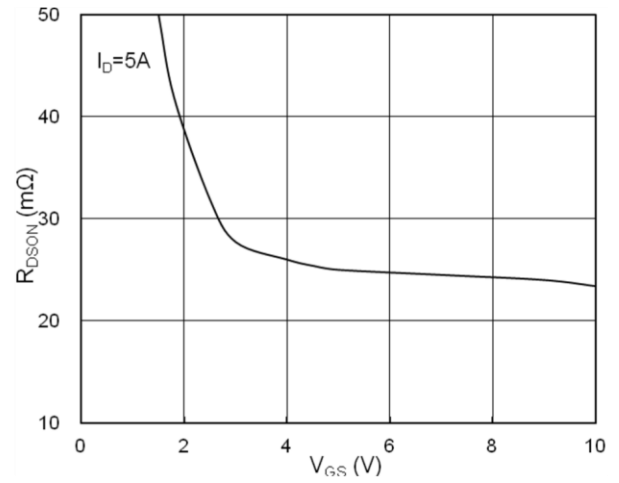


Fig.2 On-Resistance vs. Gate-Source

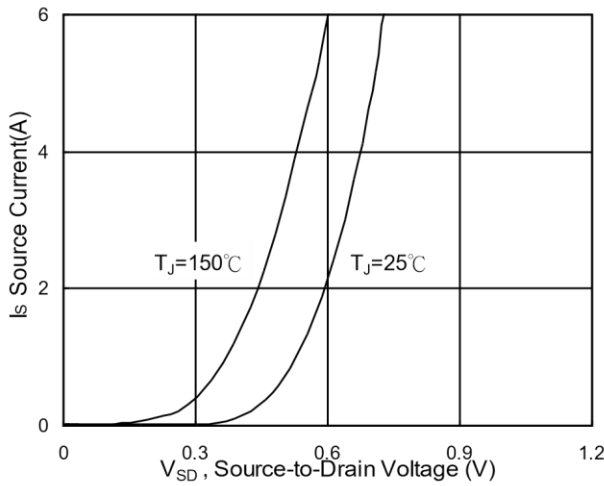


Fig.3 Forward Characteristics Of Reverse

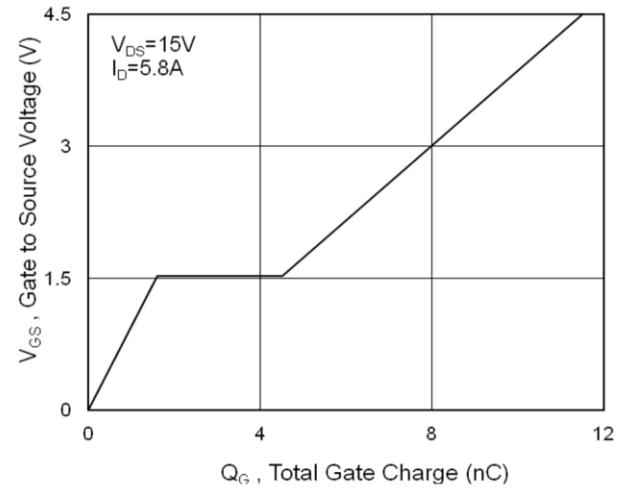


Fig.4 Gate-Charge Characteristics

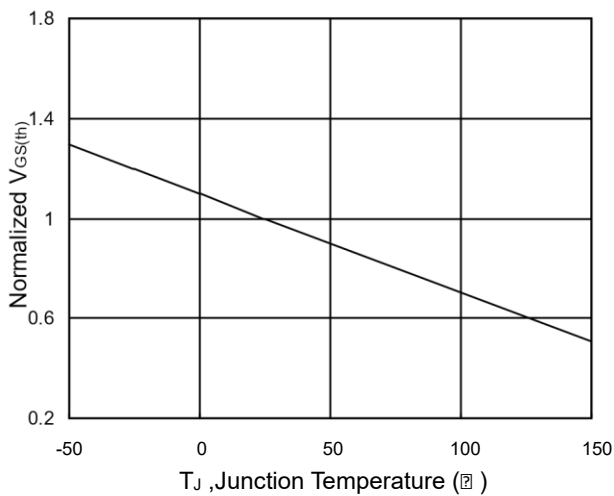


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

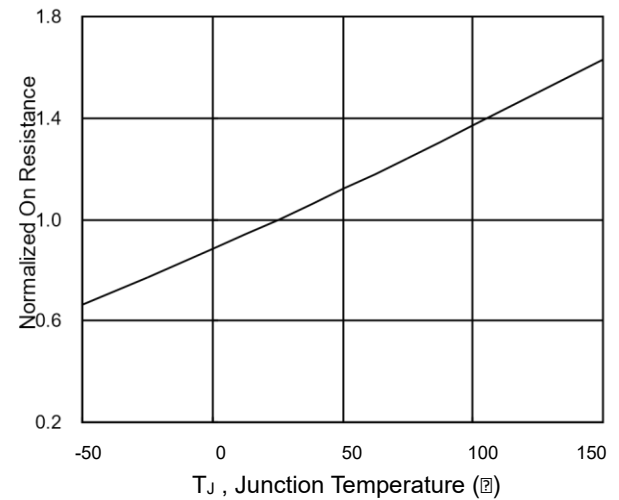


Fig.6 Normalized R_{DSON} vs. T_J



30V N-Channel Enhancement Mode MOSFET

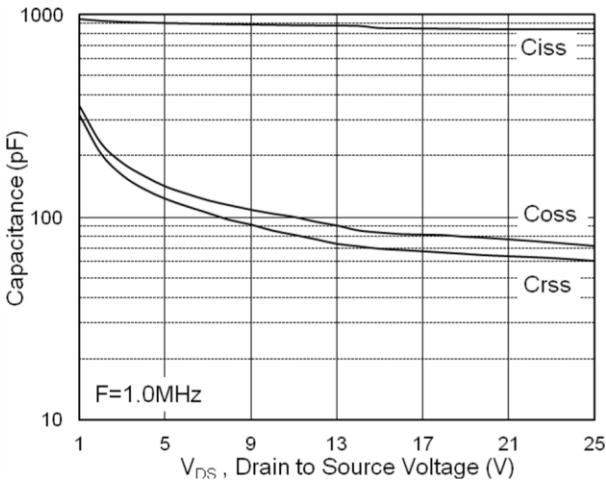


Fig.7 Capacitance

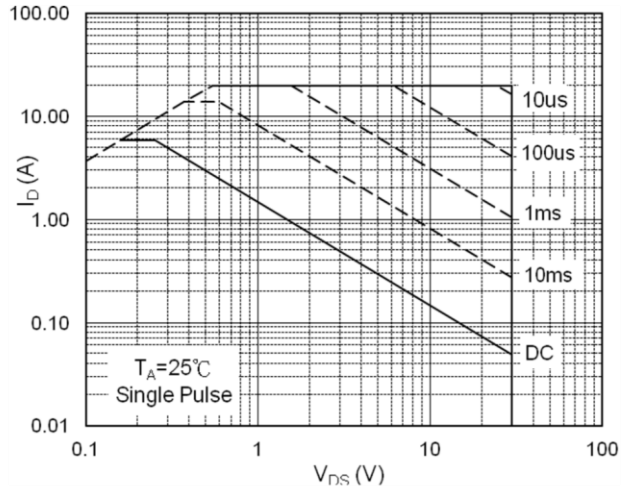


Fig.8 Safe Operating Area

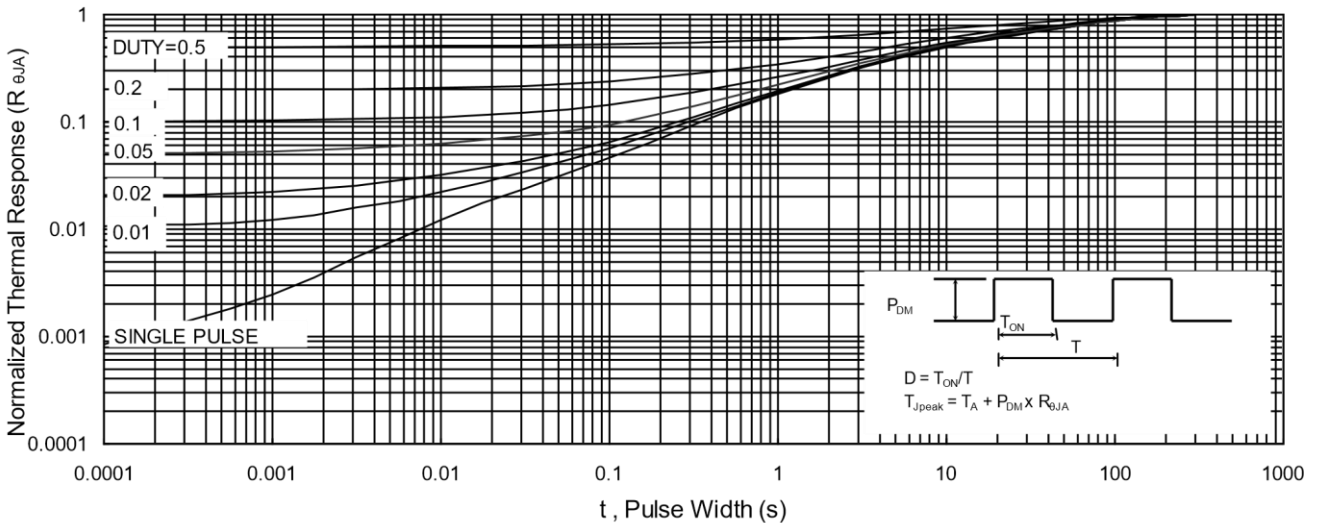


Fig.9 Normalized Maximum Transient Thermal Impedance

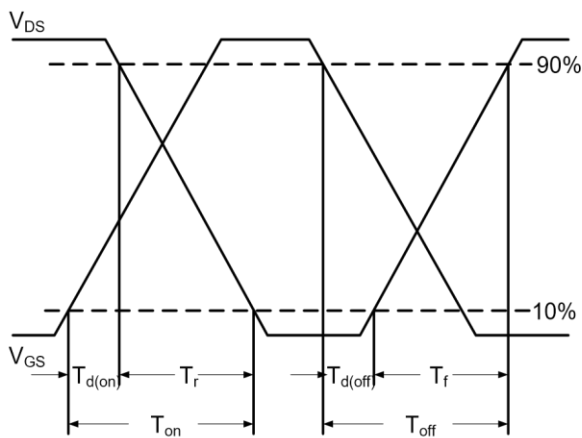


Fig.10 Switching Time Waveform

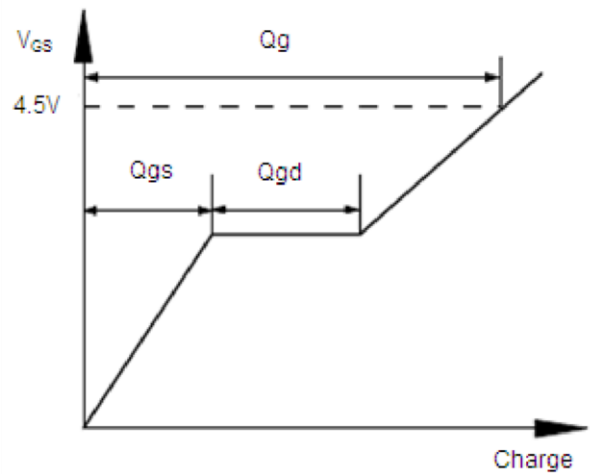
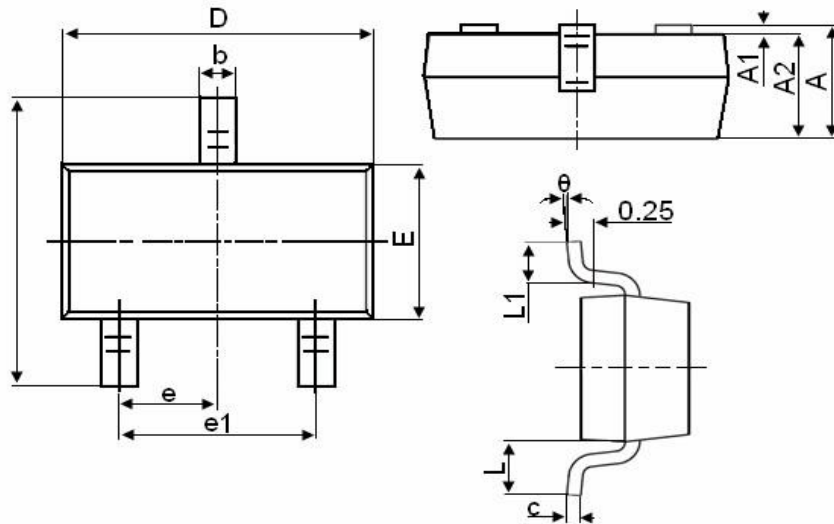


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

30V N-Channel Enhancement Mode MOSFET**Attention**

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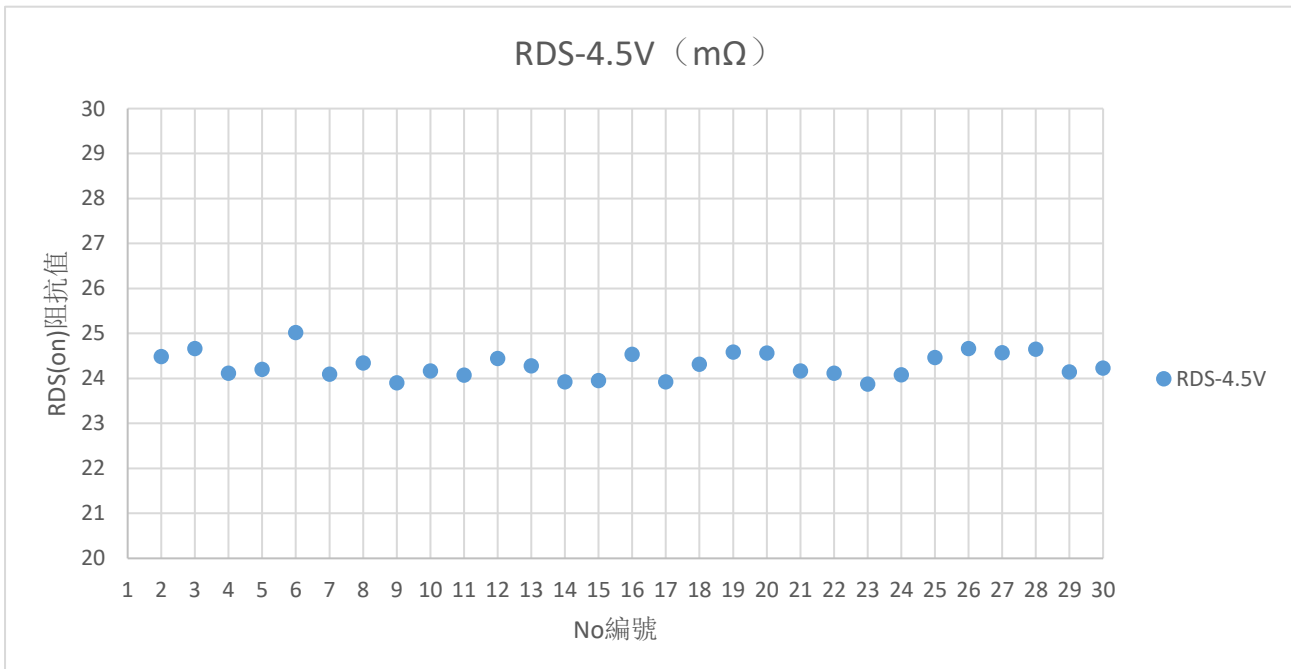
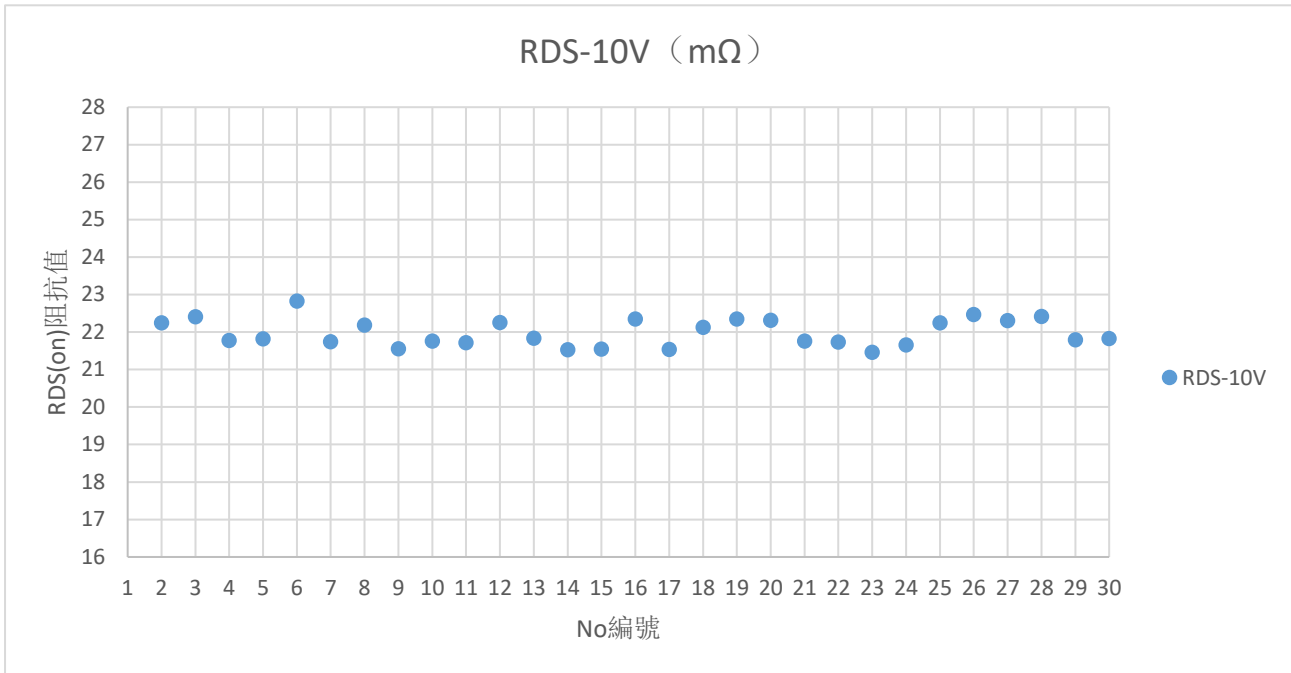
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30V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve3.0	2019/4/10	Initial release
Rve3.1	2020/3/25	Reduce RDS(on)

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Test Report For 30PCS (30pcs 典型測試報告)





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